SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME USING DAMASCENE PROCESS

ABSTRACT OF THE DISCLOSURE

A semiconductor device and method for fabricating same according to an embodiment of the invention includes: preparing a semiconductor substrate having a first contact pad and a second contact pad; forming a first insulating film on the substrate; etching the first insulating film to form a groove-shaped bit line pattern and a contact exposing the first contact pad and the second contact pad, respectively; simultaneously forming a contact plug and a bit line in the contact and the bit line pattern, respectively, the contact plug and the bitline having upper surfaces that are coplanar; and forming a bottom electrode for a capacitor that is connected to the first contact pad.